April 1988 Revised August 1999 74F413 64 x 4 First-In First-Out Buffer Memory with Parallel I/O

74F413 64 x 4 First-In First-Out Buffer Memory with Parallel I/O

General Description

FAIRCHILD

SEMICONDUCTOR

The F413 is an expandable fall-through type high-speed First-In First-Out (FIFO) buffer memory organized as 64 words by four bits. The 4-bit input and output registers record and transmit, respectively, asynchronous data in parallel form. Control pins on the input and output allow for handshaking and expansion. The 4-bit wide, 62-bit deep fall-through stack has self-contained control logic.

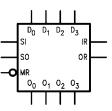
Features

- Separate input and output clocks
- Parallel input and output
- Expandable without external logic
- 15 MHz data rate
- Supply current 160 mA max
- Available in SOIC, (300 mil only)

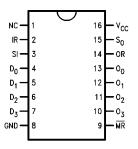
Ordering Code:

Order Number	Package Number	Package Description			
74F413PC N16E 16-Lead Pla		16-Lead Plastic Dual-In-Line Package (PDIP), JEDEC MS-001, 0.300 Wide			
Devices also available in Tape and Reel. Specify by appending the suffix letter "X" to the ordering code.					

Logic Symbol



Connection Diagram



Unit Loading/Fan Out

Pin Names	Description	U.L.	Input I _{IH} /I _{IL}
FiniNames	Description	HIGH/LOW	Output I _{OH} /I _{OL}
D ₀ -D ₃	Data Inputs	1.0/0.667	20 µA/–0.4 mA
O ₀ -O ₃	Data Outputs	50/13.3	−1 mA/8 mA
IR	Input Ready	1.0/0.667	20 µA/–0.4 mA
SI	Shift In	1.0/0.667	20 µA/–0.4 mA
SO	Shift Out	1.0/0.667	20 µA/–0.4 mA
OR	Output Ready	1.0/0.667	20 µA/–0.4 mA
MR	Master Reset	1.0/0.667	20 µA/–0.4 mA

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Functional Description

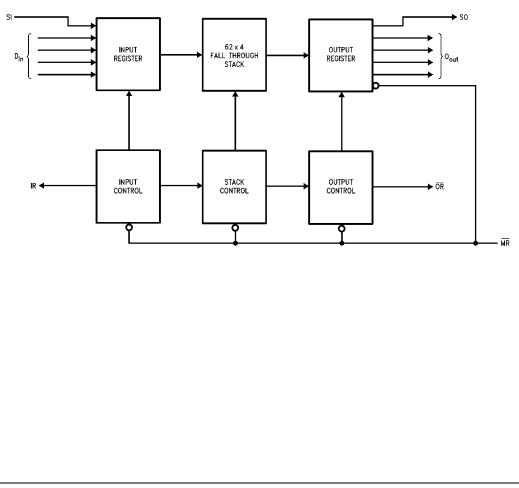
Data Input— Data is entered into the FIFO on D_0-D_3 inputs. To enter data the Input Ready (IR) should be HIGH, indicating that the first location is ready to accept data. Data then present at the four data inputs is entered into the first location when the Shift In (SI) is brought HIGH. An SI HIGH signal causes the IR to go LOW. Data remains at the first location until SI is brought LOW. When SI is brought LOW and the FIFO is not full, IR will go HIGH, indicating that more room is available. Simultaneously, data will propagate to the second location and continue shifting until it reaches the output stage or a full location. If the memory is full, IR will remain LOW.

Data Transfer— Once data is entered into the second cell, the transfer of any full cell to the adjacent (downstream) empty cell is automatic, activated by an on-chip control. Thus data will stack up at the end of the device while empty locations will "bubble" to the front. The t_{PT} parameter

defines the time required for the first data to travel from input to the output of a previously empty device.

Data Output— Data is read from the O_0 – O_3 outputs. When data is shifted to the output stage, Output Ready (OR) goes HIGH, indicating the presence of valid data. When the OR is HIGH, data may be shifted out by bringing the Shift Out (SO) HIGH. A HIGH signal at SO causes the OR to go LOW. Valid data is maintained while the SO is HIGH. When SO is brought LOW, the upstream data, provided that stage has valid data, is shifted to the output stage. When new valid data is shifted to the output stage, OR goes HIGH. If the FIFO is emptied, OR stays LOW, and O_0 – O_3 remains as before, i.e., data does not change if FIFO is empty.

Input Ready and Output Ready— may also be used as status signals indicating that the FIFO is completely full (Input Ready stays LOW for at least t_{PT}) or completely empty (Output Ready stays LOW for at least t_{PT}).



Block Diagram

Absolute Maximum Ratings(Note 1)

Storage Temperature Ambient Temperature under Bias Junction Temperature under Bias V_{CC} Pin Potential to Ground Pin Input Voltage (Note 2) Input Current (Note 2) Voltage Applied to Output in HIGH State (with $V_{CC} = 0V$) Standard Output 3-STATE Output Current Applied to Output in LOW State (Max) twice the rated I_{OL} (mA)

-65°C to +150°C -55°C to +125°C $-55^{\circ}C$ to $+150^{\circ}C$ -0.5V to +7.0V -0.5V to +7.0V -30 mA to +5.0 mA

-0.5V to V_{CC}

-0.5V to +5.5V

Recommended Operating Conditions

Free Air Ambient Temperature Supply Voltage

 $0^{\circ}C$ to $+70^{\circ}C$ +4.5V to +5.5V

Note 1: Absolute maximum ratings are values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

Note 2: Either voltage limit or current limit is sufficient to protect inputs.

DC Electrical Characteristics

Symbol Parameter Min Тур Max Units v_{cc} Conditions VIH Input HIGH Voltage 2.0 V Recognized as a HIGH Signal Input LOW Voltage Recognized as a LOW Signal V_{IL} 0.8 V $I_{IN} = -18 \text{ mA}$ Input Clamp Diode Voltage V_{CD} -1.5 ٧ Min VOH $I_{OH} = -1 \text{ mA}$ Output HIGH 2.4 10% V_{CC} V Min Voltage 5% V_{CC} 2.7 $I_{OH} = -1 \text{ mA}$ 10% V_{CC} VOL Output LOW Voltage 0.5 V Min $I_{OL} = 8 \text{ mA}$ $V_{IN} = 2.7V$ $I_{\rm IH}$ Input HIGH Current 5.0 μA Max Input HIGH Current I_{BVI} 7.0 μΑ $V_{IN} = 7.0V$ Max Breakdown Test $V_{OUT} = V_{CC}$ ICEX Output HIGH Leakage Current 50 μΑ Max V_{ID} Input Leakage $I_{ID} = 1.9 \ \mu A$ v 4.75 0.0 Test All Other Pins Grounded V_{IOD} = 150 mV Output Leakage I_{OD} 3.75 μΑ 0.0 Circuit Current All Other Pins Grounded Input LOW Current -0.4 mΑ Max $V_{IN} = 0.5V$ $I_{\rm IL}$ Max Output Short-Circuit Current -20 -130 $V_{OUT} = 0V$ los mΑ $\overline{V_0 = HIGH}$ Power Supply Current 160 Max 115 mΑ I_{CCH}

74F413

AC Electrical Characteristics

$T_A = -55^{\circ}C \text{ to } +125^{\circ}C$ $T_A = 0^\circ \text{ to } +70^\circ C$ $\textbf{T}_{\textbf{A}}=+25^{\circ}\textbf{C}$ $V_{CC} = +5.0V$ $V_{CC} = +5.0V$ $V_{CC} = +5.0V$ Symbol Units Parameter $C_L = 50 \ pF$ $C_L = 50 \ pF$ $C_L = 50 \ pF$ Min Тур Max Min Max Min Max MHz Shift In Rate 10 8.0 10 $\mathsf{f}_{\mathsf{MAX}}$ Shift Out Rate 10 8.0 10 MHz $\mathsf{f}_{\mathsf{MAX}}$ Propagation Delay 1.5 44.0 1.5 50.0 1.5 48.0 t_{PLH} ns Shift In to IR 1.5 31.0 1.5 37.0 1.5 35.0 t_{PHL} Propagation Delay 1.5 52.0 1.5 57.0 1.5 55.0 t_{PLH} ns 37.0 35.0 Shift Out to OR 1.5 1.5 1.5 31.0 t_{PHL} Propagation Delay 1.5 46.0 1.5 52.0 1.5 50.0 t_{PLH} ns Output Data Delay 1.5 34.0 1.5 39.0 1.5 37.0 t_{PHL} Propagation Delay 1.5 27.0 1.5 33.0 1.5 31.0 ns t_{PLH} Master Reset to IR 30.0 1.5 34.0 1.5 32.0 1.5 t_{PLH} Propagation Delay ns Master Reset to OR

AC Operating Requirements

Symbol	Parameter	T _A = +25°C V _{CC} = +5.0V	$T_A = -55^{\circ}C \text{ to } +125^{\circ}C$ $V_{CC} = +5.0V$	$T_A = 0^\circ \text{ to } +70^\circ \text{C}$ $V_{CC} = +5.0 \text{V}$	Units
		Min Max	Min Max	Min Max	
t _S (H)	Setup Time, HIGH or LOW	1.0	1.0	1.0	ns
t _S (L)	D _n to SI	1.0	1.0	1.0	
t _H (H)	Hold Time, HIGH or LOW	10.0	10.0	10.0	1
t _H (L)	D _n to SI	10.0	10.0	10.0	
t _W (H)	Shift In Pulse Width	5.0	5.0	5.0	ns
t _W (L)	HIGH or LOW	10.0	10.0	10.0	
t _W (H)	Shift Out Pulse Width	7.5	8.5	7.5	1
t _W (L)	HIGH or LOW	10.0	10.0	10.0	
t _W (H)	Input Ready Pulse Width,	7.5	8.5	7.5	ns
	HIGH				
t _W (L)	Output Ready Pulse Width,	5.0	5.0	5.0	ns
	LOW				
t _W (L)	Master Reset Pulse Width,	10.0	10.0	10.0	ns
	LOW				
t _{REC}	Recovery Time, MR to SI	32.0	35.0	35.0	ns
t _{PT}	Data Throughput Time	0.9	1.0	1.0	μs

